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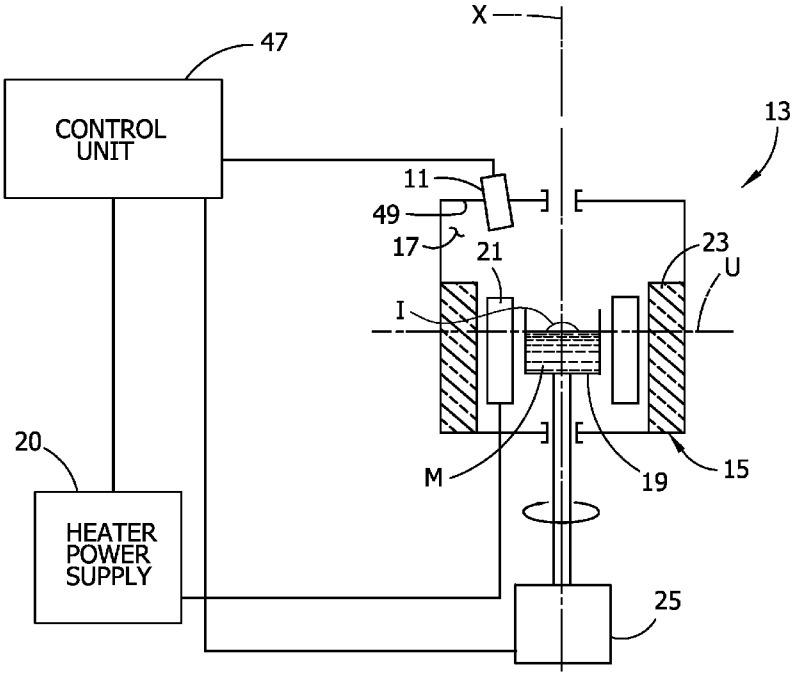
[Continued on next page]

(54) **Title**: METHOD AND DEVICE FOR CONTINUOUSLY MEASURING SILICON ISLAND ELEVATION

FIG. 1



(57) **Abstract**: A method of continuously measuring an elevation and shape of an unmelted polycrystalline silicon island during a silicon meltdown process. The method comprises projecting a focused bright light on the silicon island to produce a bright dot on the silicon island. The method also includes electronically determining an elevation and a shape of the silicon island by tracking the bright dot during the meltdown process.

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